Elektronische Bauelemente

SCS222DSTL

0.1A , 80V

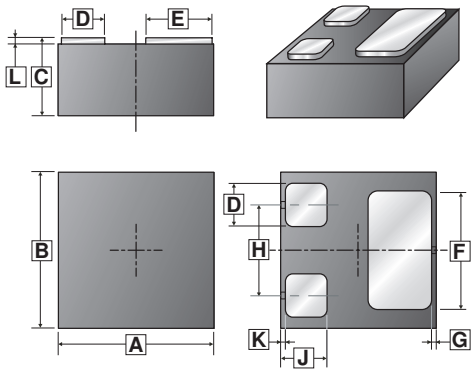
Plastic-Encapsulated Switching Diode

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

- Epitaxial planar Silicon diode

WBFBP-03D



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.950	1.050	G	-	0.050
B	0.950	1.050	H	0.510	0.610
C	0.010	0.070	J	0.250	0.350
D	0.210	0.310	K	-	0.050
E	0.350 REF.		L	0.450	0.550
F	0.680 REF.				

FEATURES

- High speed. (T_{RR}=1.5ns Typ.)
- Suitable for high packing density layout
- High reliability.

APPLICATIONS

- Ultra high speed switching
- For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING

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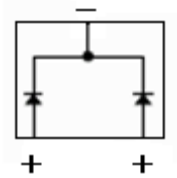
PACKAGE INFORMATION

Package	MPQ	Leader Size
WBFBP-03D	5K	7 inch

TOP VIEW



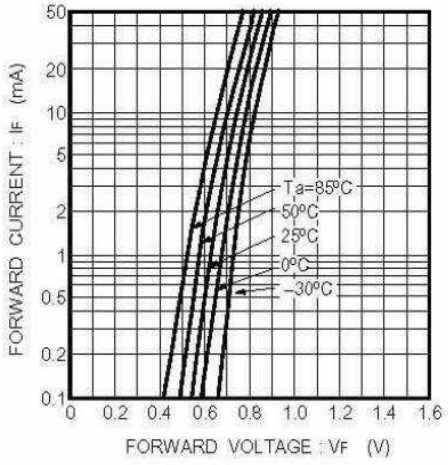
ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameters	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	100	mW
Operating Junction and Storage Temperature	T_J,T_{STG}	150, -65~150	℃

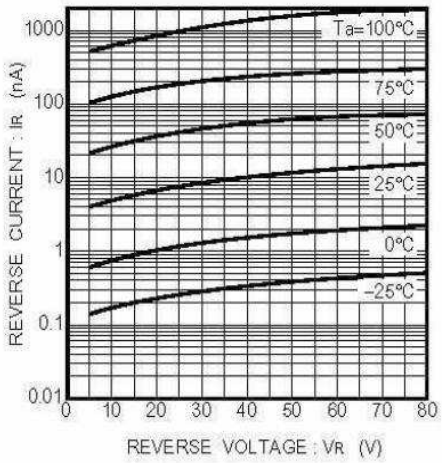
ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Reverse breakdown voltage	$V_{(BR)}$	80	-	V	I_R=100μA
Maximum DC Reverse Current at rated DC blocking voltage	I_R	-	0.1	μA	V_R=70V
Forward Voltage	V_F	-	1.2	V	I_F=100mA
Diode Capacitance	C_D	-	3.5	pF	V_R=6V, f=1MHz
Maximum Reverse Recovery Time	T_{RR}	-	4	nS	V_R=6V, I_F=5mA

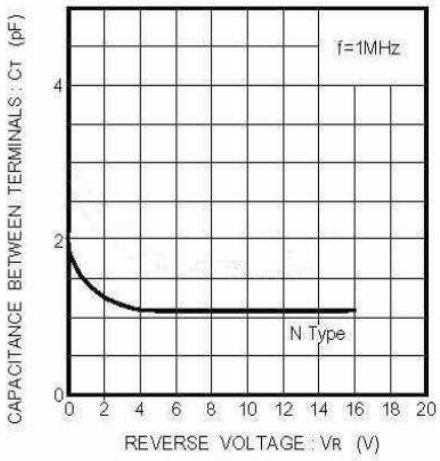
CHARACTERISTIC CURVES



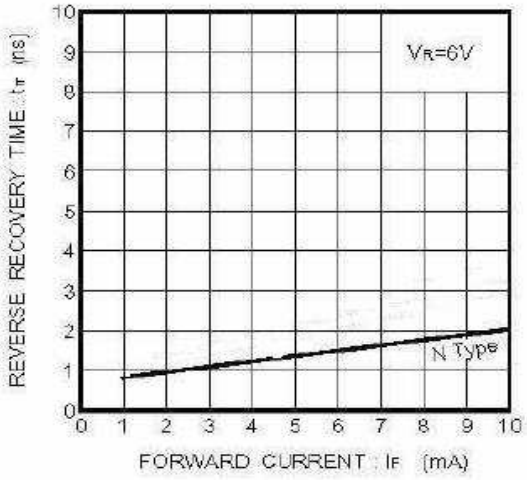
Forward characteristics



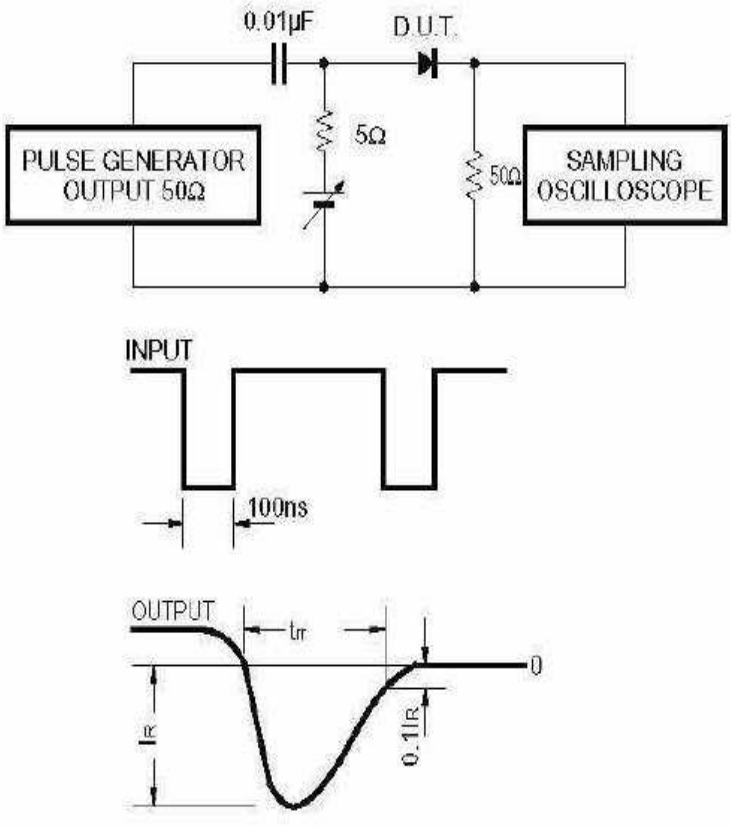
Reverse characteristics



Capacitance between terminals characteristics



Reverse recovery time



Reverse recovery time (t_{rr}) measurement circuit

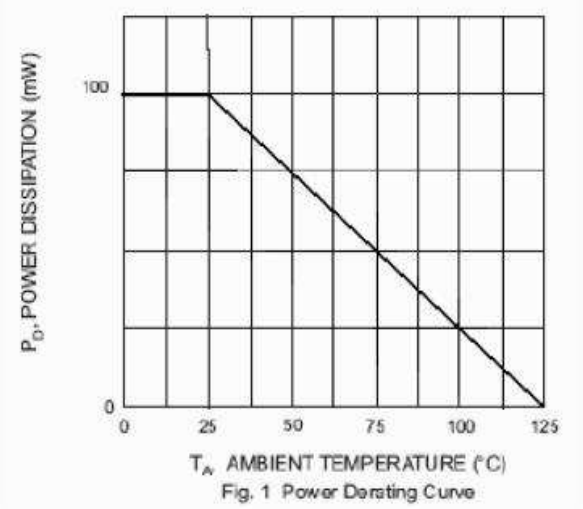


Fig. 1 Power Derating Curve